Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

NSCT3906LT1G

General Purpose Transistors

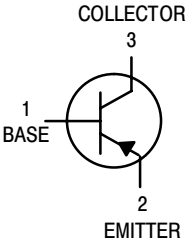
PNP Silicon

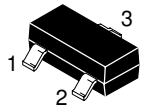
ON Semiconductor®

http://onsemi.com

Features

- These are Pb−Free Devices





SOT−23
CASE 318
STYLE 6

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector − Emitter Voltage	V_{CEO}	−40	Vdc
Collector − Base Voltage	V_{CBO}	−40	Vdc
Emitter − Base Voltage	V_{EBO}	−5.0	Vdc
Collector Current − Continuous	I_C	−200	mAdc

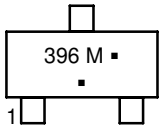
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board (Note 1) @ T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) @ T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR−5 = 1.0 × 0.75 × 0.062 in.
2. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.

MARKING DIAGRAM



396 = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
NSCT3906LT1G	SOT−23 (Pb−Free)	3,000 Tape & Reel
NSCT3906LT3G	SOT−23 (Pb−Free)	10,000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (I_C = –1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	–40	–	Vdc
Collector – Base Breakdown Voltage (I_C = –10 μAdc, I_E = 0)	$V_{(BR)CBO}$	–40	–	Vdc
Emitter – Base Breakdown Voltage (I_E = –10 μAdc, I_C = 0)	$V_{(BR)EBO}$	–5.0	–	Vdc
Base Cutoff Current (V_{CE} = –30 Vdc, V_{EB} = –3.0 Vdc)	I_{BL}	–	–50	nAdc
Collector Cutoff Current (V_{CE} = –30 Vdc, V_{EB} = –3.0 Vdc)	I_{CEX}	–	–50	nAdc
ON CHARACTERISTICS (Note 3)				
DC Current Gain (I_C = –0.1 mAdc, V_{CE} = –1.0 Vdc) (I_C = –1.0 mAdc, V_{CE} = –1.0 Vdc) (I_C = –10 mAdc, V_{CE} = –1.0 Vdc) (I_C = –50 mAdc, V_{CE} = –1.0 Vdc) (I_C = –100 mAdc, V_{CE} = –1.0 Vdc)	H_{FE}	 60 80 100 60 30	 – – 300 – –	–
Collector – Emitter Saturation Voltage (I_C = –10 mAdc, I_B = –1.0 mAdc) (I_C = –50 mAdc, I_B = –5.0 mAdc)	$V_{CE(sat)}$	 – –	 –0.25 –0.4	Vdc
Base – Emitter Saturation Voltage (I_C = –10 mAdc, I_B = –1.0 mAdc) (I_C = –50 mAdc, I_B = –5.0 mAdc)	$V_{BE(sat)}$	 –0.65 –	 –0.85 –0.95	Vdc
SMALL–SIGNAL CHARACTERISTICS				
Current – Gain – Bandwidth Product (I_C = –10 mAdc, V_{CE} = –20 Vdc, f = 100 MHz)	f_T	250	–	MHz
Output Capacitance (V_{CB} = –5.0 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	–	4.5	pF
Input Capacitance (V_{EB} = –0.5 Vdc, I_C = 0, f = 1.0 MHz)	C_{ibo}	–	10	pF
Input Impedance (I_C = –1.0 mAdc, V_{CE} = –10 Vdc, f = 1.0 kHz)	h_{ie}	2.0	12	kΩ
Voltage Feedback Ratio (I_C = –1.0 mAdc, V_{CE} = –10 Vdc, f = 1.0 kHz)	h_{re}	0.1	10	X 10^{-4}
Small – Signal Current Gain (I_C = –1.0 mAdc, V_{CE} = –10 Vdc, f = 1.0 kHz)	h_{fe}	100	400	–
Output Admittance (I_C = –1.0 mAdc, V_{CE} = –10 Vdc, f = 1.0 kHz)	h_{oe}	3.0	60	μmhos
Noise Figure (I_C = –100 μAdc, V_{CE} = –5.0 Vdc, R_S = 1.0 kΩ, f = 1.0 kHz)	NF	–	4.0	dB
SWITCHING CHARACTERISTICS				
Delay Time	(V_{CC} = –3.0 Vdc, V_{BE} = 0.5 Vdc, I_C = –10 mAdc, I_{B1} = –1.0 mAdc)	t_d	–	35	ns
Rise Time		t_r	–	35	
Storage Time	(V_{CC} = –3.0 Vdc, I_C = –10 mAdc, I_{B1} = I_{B2} = –1.0 mAdc)	t_s	–	225	ns
Fall Time		t_f	–	75	

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

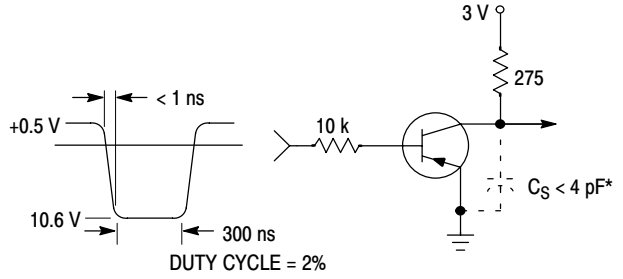


Figure 1. Delay and Rise Time Equivalent Test Circuit

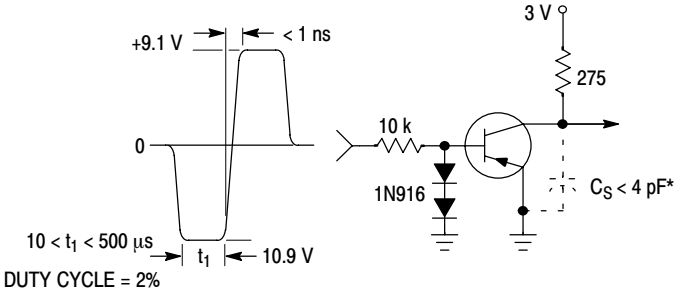


Figure 2. Storage and Fall Time Equivalent Test Circuit

* Total shunt capacitance of test jig and connectors

TYPICAL TRANSIENT CHARACTERISTICS

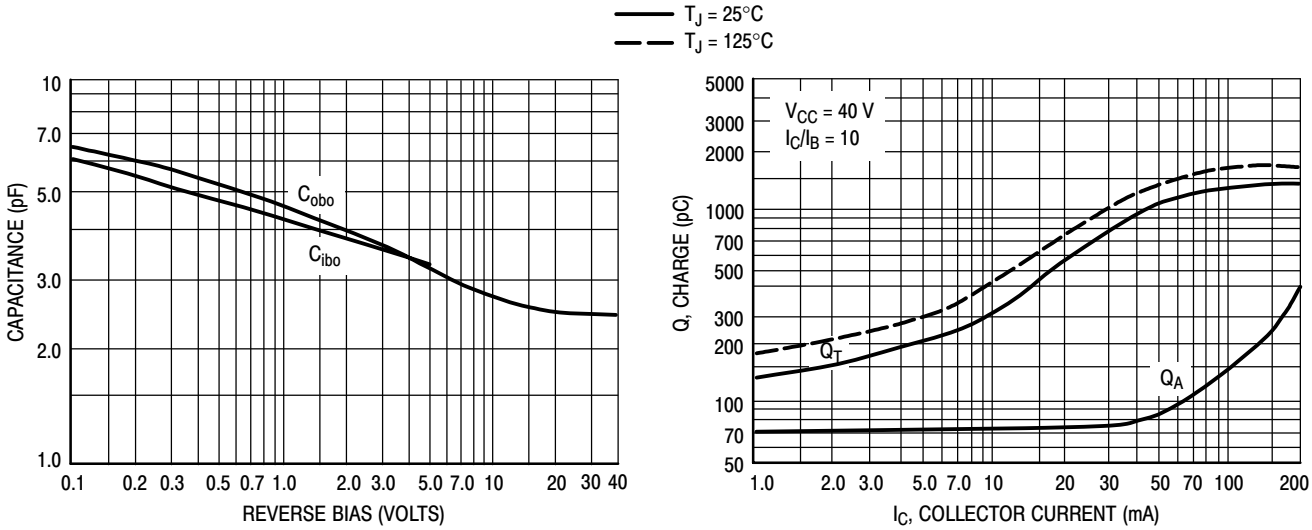


Figure 3. Capacitance

Figure 4. Charge Data

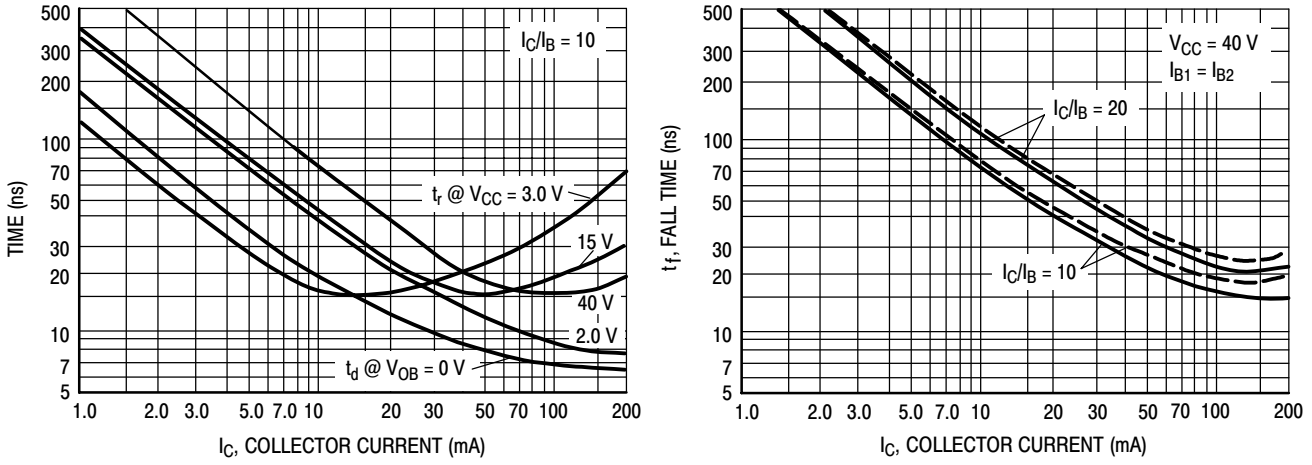


Figure 5. Turn−On Time

Figure 6. Fall Time

TYPICAL AUDIO SMALL−SIGNAL CHARACTERISTICS
NOISE FIGURE VARIATIONS

(V_{CE} = −5.0 Vdc, T_A = 25°C, Bandwidth = 1.0 Hz)

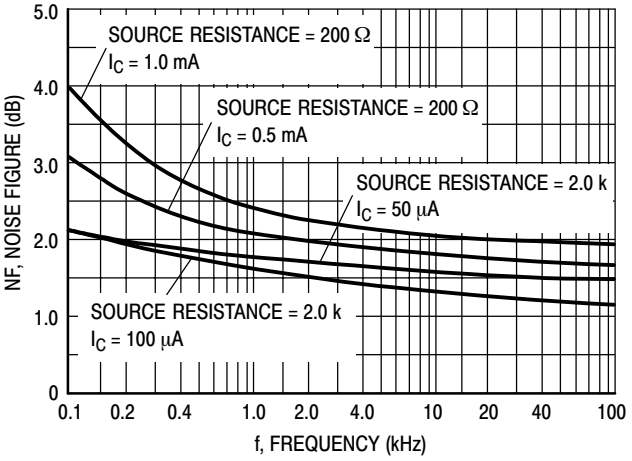


Figure 7.

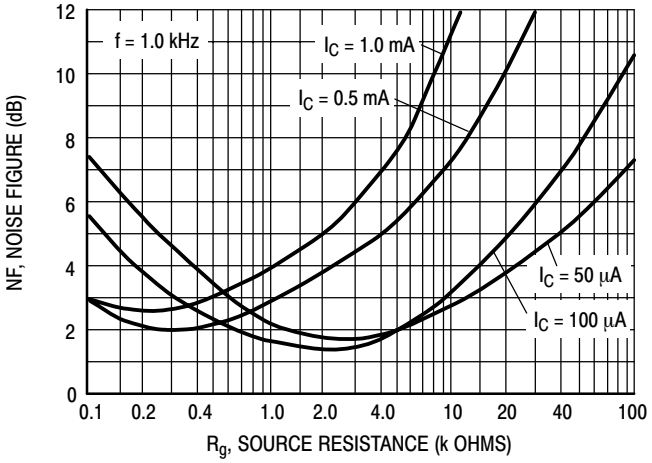


Figure 8.

h PARAMETERS

(V_{CE} = −10 Vdc, f = 1.0 kHz, T_A = 25°C)

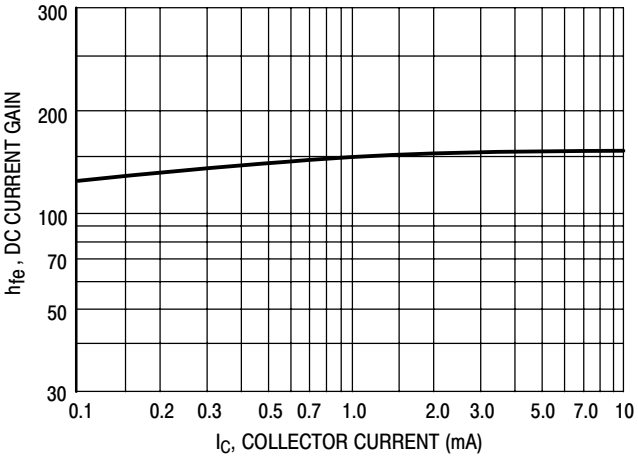


Figure 9. Current Gain

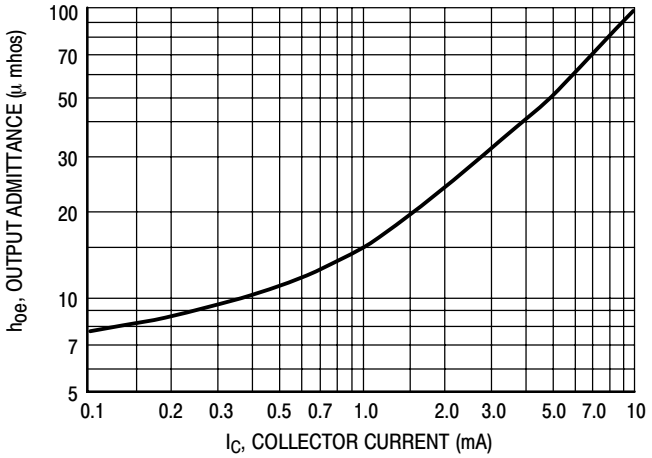


Figure 10. Output Admittance

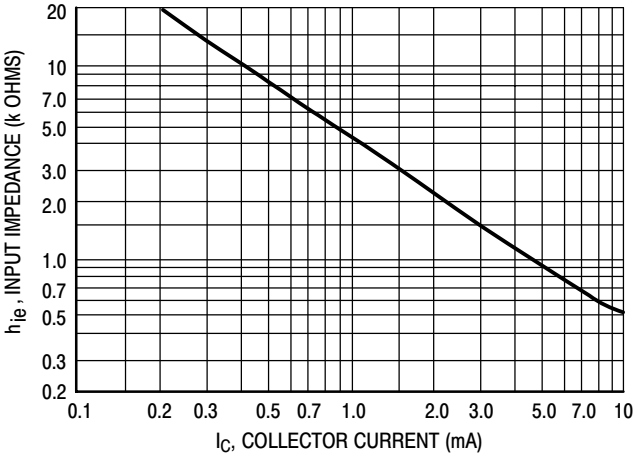


Figure 11. Input Impedance

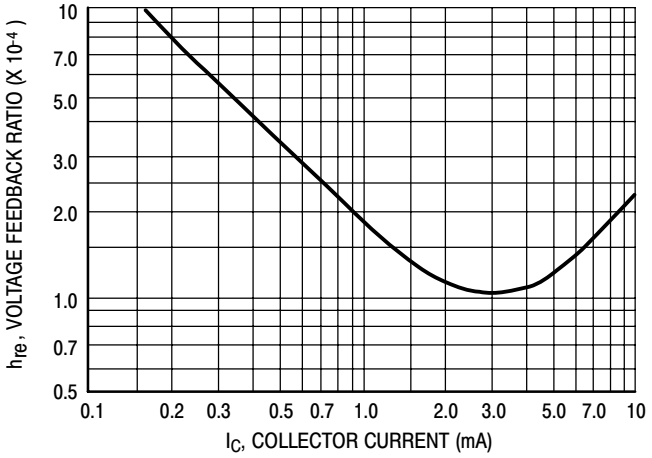


Figure 12. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

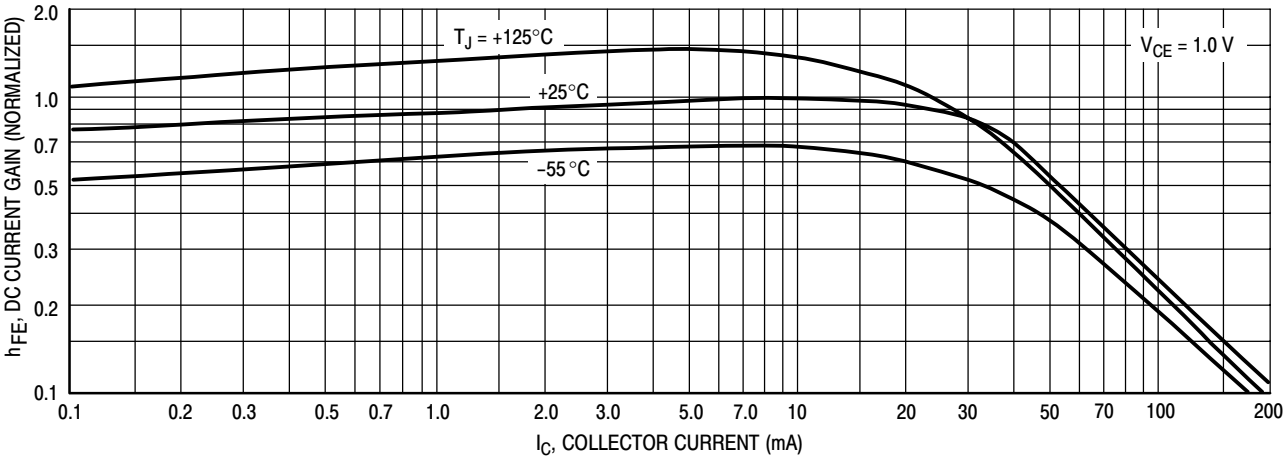


Figure 13. DC Current Gain

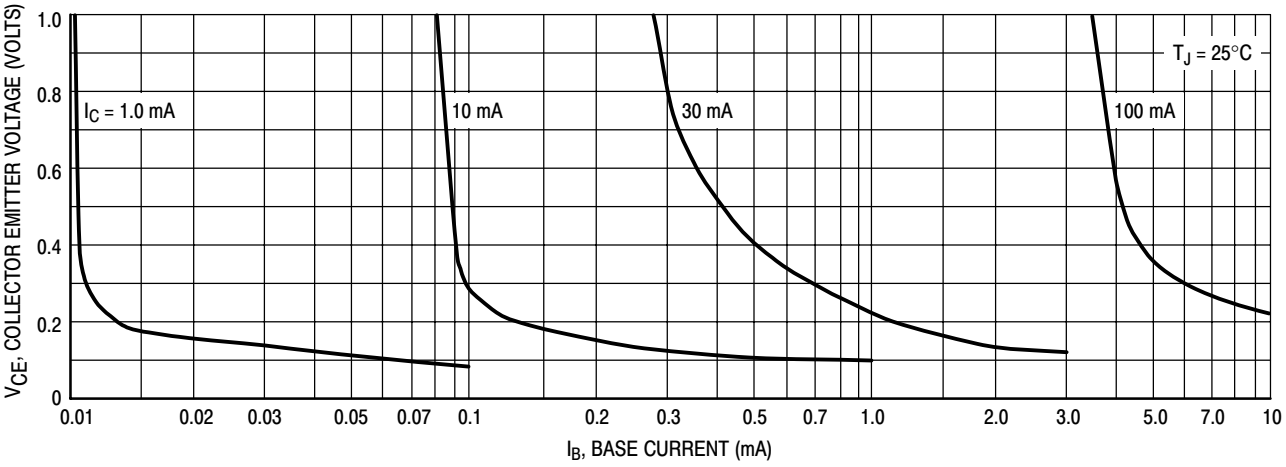


Figure 14. Collector Saturation Region

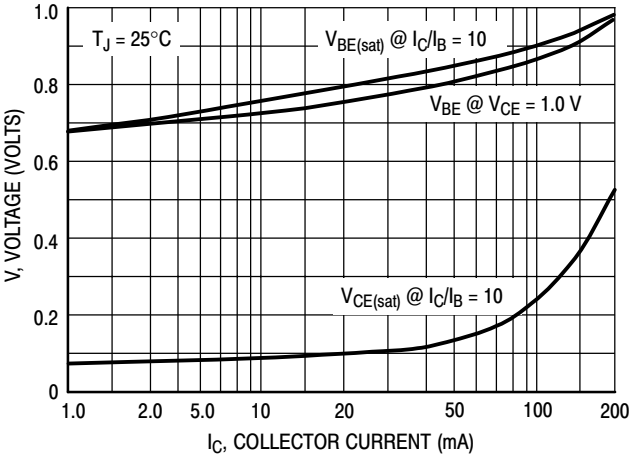


Figure 15. "ON" Voltages

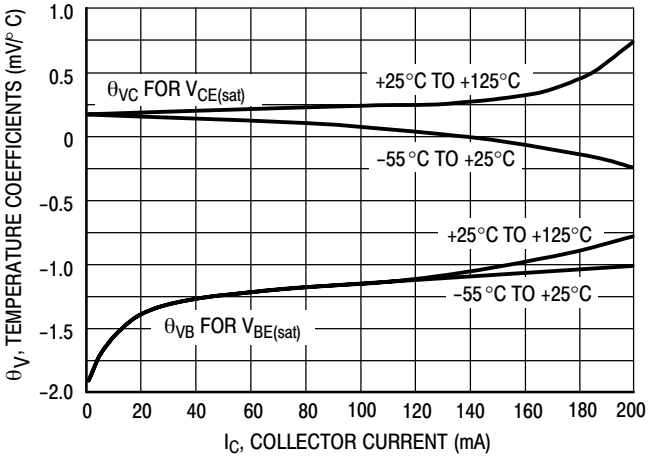
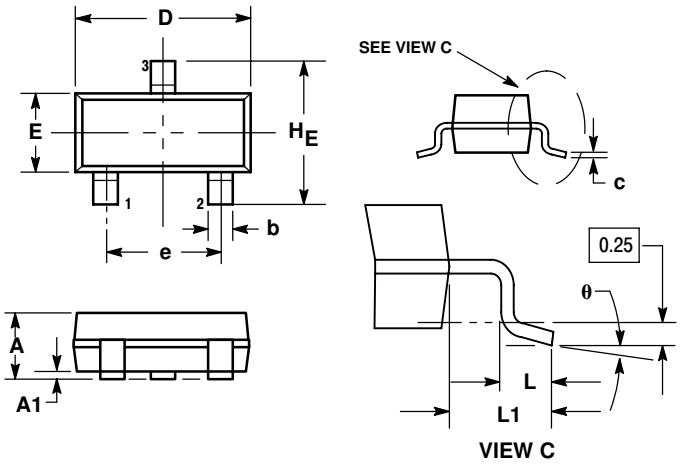


Figure 16. Temperature Coefficients

NSCT3906LT1G

PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−08
ISSUE AN

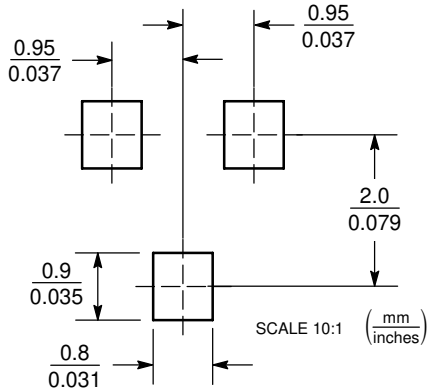


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318−01 THRU −07 AND −09 OBSOLETE, NEW STANDARD 318−08.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
H_E	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082−1312 USA
Phone: 480−829−7710 or 800−344−3860 Toll Free USA/Canada
Fax: 480−829−7709 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2−9−1 Kamimeguro, Meguro−ku, Tokyo, Japan 153−0051
Phone: 81−3−5773−3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.